/ Descriptions

WR0<5 ṂṂ Ḅ SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

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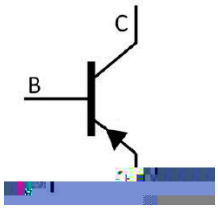
Low Leakage current, Low collector saturation voltage.

/ Applications

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General amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 χ Collector PIN 2 χ Base PIN 3 χ Emitter

/ hFE Classifications & Marking

ծ м ヽ ب ˝ See Marking Instructions.

v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_CCollecto78.22.1(ent		

2N2907

Rev. G .Aug.-2018

DATA SHEET

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ў 25 Ќ 150 ł ı `H ڑ 60 Ќ 90sec;

2 Š Ө □ ў 255 ° 5 ł ı `H ڑ `Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ѡ ў ㎛ 2 Ќ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ў χ 270 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

¨Ω ţ ϒ Ł / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

ﾊ Ѵ ϒ Ł / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235， 大箱 547×407×268

/ Notices